## Paper / Subject Code: 51202 / Electronics Devices and Circuits-I

14-May-19 1T01023 - S.E.(ELECTRONICS & TELE-COMMN)(Sem III) (Choice Based) / 51202 - ELECTRONIC DEVICES & CIRCUITS I 59116

(Time: 3 Hours) Marks: 80

- N.B.: (1) Question No. 1 is compulsory.
  - (2) Solve any three questions from the remaining five
  - (3) Figures to the right indicate full marks
  - (4) Assume suitable data if necessary and mention the same in answer sheet.
- Q.1 Attempt any 4 questions.

[20]

- (a) Explain bleeder resistor and critical inductance.
- (b) Explain zero temperature drift biasing.
- (c) Explain effect of bypass capacitor and coupling capacitors on frequency response of amplifier
- (d) Draw and explain high frequency model of BJT for CE configuration.
- (e) Draw and explain small signal model of FET.
- Q.2 (a) Design single stage *RC* coupled CS amplifier using self-bias method to meet following specifications: |Av| = 18, Vo = 2.5 Vrms,  $I_{DSS} = 7$  mA,  $g_{mo} = 5600$   $\mu$ S, Vp = 2.5 V,  $r_d = 50$  k $\Omega$ .
  - (b) Calculate Av, Zi and Zo for the circuit designed in Q.2(a).

[05]

- Q.3 (a) A full wave rectifier using a centre tapped transformer with two diodes gives output of 250 V and current is 100 +/- 25 mA. If the ripple factor is 0.001. Calculate the specification of the devices and components required if the filter used is *LC* filter.
  - (b) Explain the basic fabrication steps of passive elements.

[08]

[05]

- Q.4 (a) What is biasing? What is the need of biasing? Derive the expression for stability [10] factor of collector to base bias circuit.
  - (b) Calculate Q-point ( $I_{CQ} \& V_{CEQ}$ ) and stability factor (S) for the circuit shown in [10] Fig. 4(b).

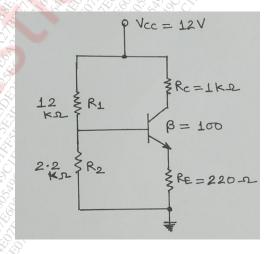


Fig. 4(b)

- Q.5 (a) Derive the expressions for Ai, Av, Zi, Zo for CE amplifier with unbypassed  $R_E$ . [15]
  - (b) State and explain Miller's Theorem.

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Q.6 (a) Sketch the frequency response for the circuit shown Fig. 6(a) where [15]  $C_1 = 0.5 \, \mu\text{F}$ ,  $C_2 = 1 \, \mu\text{F}$ ,  $C_S = 10 \, \mu\text{F}$ ,  $C_{gs} = 5 \, \text{pF}$ ,  $C_{gd} = 2 \, \text{pF}$ ,  $C_{ds} = 3 \, \text{pF}$ . Take  $I_D = 3 \, \text{mA}$ .

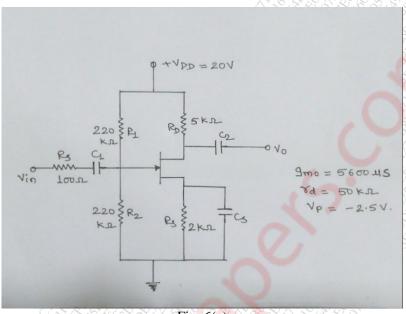


Fig. 6(a)

(b) Write a short note on small signal model of diode.

[05]



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